**Product data sheet** 

# 1. General description

Silicon Carbide Schottky diode in a TO220-2L plastic package, designed for high frequency switched-mode power supplies.



### 2. Features and benefits

- · Highly stable switching performance
- Extremely fast reverse recovery time
- · Superior in efficiency to Silicon Diode alternatives
- · Reduced losses in associated MOSFET
- Reduced EMI
- · Reduced cooling requirements
- RoHS compliant

# 3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

### 4. Quick reference data

#### Table 1. Quick reference data

| Symbol             | Parameter                       | Conditions   | Notes | s Values      |      |      | Unit |  |
|--------------------|---------------------------------|--|-------|---------------|------|------|------|--|
| Absolute           | Absolute maximum rating         |  |       |               |      |      |      |  |
| $V_{RRM}$          | repetitive peak reverse voltage |  |       | 650           |      |      | V    |  |
| I <sub>F(AV)</sub> | average forward current         | $\delta$ = 0.5; square-wave pulse; T <sub>mb</sub> ≤ 136 °C;<br>Fig. 1; Fig. 2; Fig. 3                               |       | 6             |      | А    |      |  |
| T <sub>j</sub>     | junction temperature            |  |       | -55 to 175 °C |      |      | °C   |  |
| Symbol             | Parameter                       | Conditions   | Notes | Min           | Тур  | Max  | Unit |  |
| Static ch          | aracteristics                   |  |       |               |      |      |      |  |
| V <sub>F</sub>     | forward voltage                 | I <sub>F</sub> = 6 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>  |       | -             | 1.45 | 1.70 | V    |  |
|                    |                                 | I <sub>F</sub> = 6 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>   |       | -             | 1.80 | 2.20 | V    |  |
| Dynamic            | Dynamic characteristics         |  |       |               |      |      |      |  |
| Q <sub>r</sub>     | recovered charge                | $I_F = 6 \text{ A}$ ; $dI_F/dt = 500 \text{ A/}\mu\text{s}$ ; $V_R = 400 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7 |       | -             | 9    | -    | nC   |  |

# 5. Pinning information

### **Table 2. Pinning information**

| Pin | Symbol | Description                         | Simplified outline | Graphic symbol                  |
|-----|--------|-------------------------------------|--------------------|---------------------------------|
| 1   | K      | cathode                             | mb                 | K 14 A                          |
| 2   | Α      | anode                               | }                  | K <del>   </del> A<br>001aaa020 |
| mb  | mb     | mounting base; connected to cathode |                    |                                 |

# 6. Ordering information

**Table 3. Ordering information** 

| Type number | Package name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date |
|-------------|--------------|-----------------------|----------------|------------------------|-----------------|--------------------|
| WNSC5D06650 | TO220-2L     | WNSC5D066506Q         | Tube           | 50                     | SOD59A          | 30-Mar-2015        |

# 7. Marking

#### Table 4. Marking codes

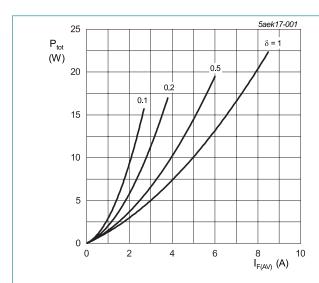
| Type number | Marking codes   |
|-------------|-----------------|
| WNSC5D06650 | WNSC5D<br>06650 |

# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol             | Parameter                       | Conditions  | Notes | Values     | Unit             |
|--------------------|---------------------------------|---|-------|------------|------------------|
| $V_{RRM}$          | repetitive peak reverse voltage |   |       | 650        | V                |
| $V_{\text{RWM}}$   | crest working reverse voltage   |   |       | 650        | V                |
| $V_R$              | reverse voltage                 | DC  |       | 650        | V                |
| I <sub>F(AV)</sub> | average forward current         | $\delta$ = 0.5; square-wave pulse; $T_{mb} \le 136$ °C;<br>Fig. 1; Fig. 2; Fig. 3 |       | 6          | А                |
| I <sub>FRM</sub>   | repetitive peak forward current | $\delta$ = 0.5; $t_p$ = 25 μs; $T_{mb}$ ≤ 136 °C; square-wave pulse               |       | 12         | Α                |
| I <sub>FSM</sub>   | non-repetitive peak             | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse                             |       | 40         | А                |
|                    | forward current                 | $t_p$ = 10 $\mu$ s; $T_{j(init)}$ = 25 °C; square-wave pulse                      |       | 310        | А                |
| l <sup>2</sup> t   | I <sup>2</sup> t for fusing     | sine-wave pulse; $T_{j(init)} = 25  ^{\circ}C$ ; $t_p = 10  \text{ms}$            |       | 8          | A <sup>2</sup> s |
| T <sub>stg</sub>   | storage temperature             |   |       | -55 to 175 | °C               |
| T <sub>j</sub>     | junction temperature            |   |       | -55 to 175 | °C               |



$$\begin{split} & |_{F(AV)} = |_{F(RMS)} \times \sqrt{\delta} \\ & V_o = 1.142 \text{ V; } R_s = 0.1756 \text{ }\Omega \end{split}$$
 Fig. 1. Forward power dissipation as a function of average forward current; square waveform;

maximum values

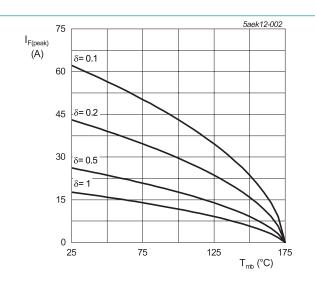
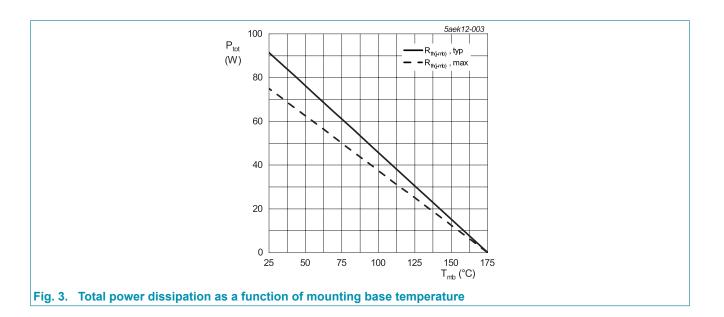


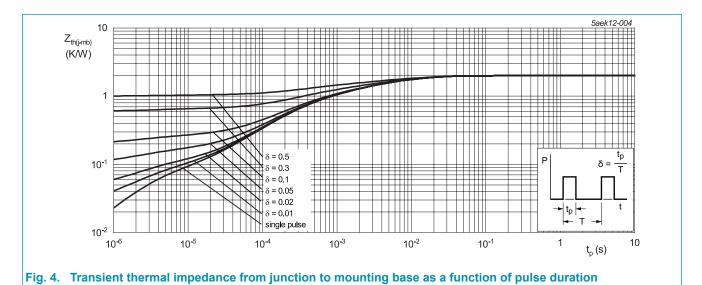
Fig. 2. Current derating as a function of mounting base temperature



## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

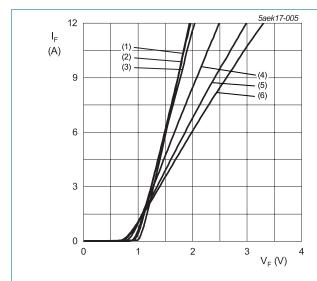
| Symbol                | Parameter  | Conditions                     | Notes | Min | Тур  | Max | Unit |
|-----------------------|--|--------------------------------|-------|-----|------|-----|------|
| $R_{\text{th(j-mb)}}$ | thermal resistance<br>from junction to<br>mounting base    | with heatsink compound; Fig. 4 |       | -   | 1.64 | 2   | K/W  |
| $R_{\text{th(j-a)}}$  | thermal resistance<br>from junction to<br>ambient free air | in free air                    |       | -   | 50   | -   | K/W  |



## 10. Characteristics

Table 7. Characteristics

| Symbol          | Parameter                       | eter Conditions   |  | Min | Тур  | Max  | Unit |
|-----------------|---------------------------------|---|--|-----|------|------|------|
| Static cha      | aracteristics                   |   |  |     | •    |      |      |
| $V_{F}$         | forward current                 | I <sub>F</sub> = 6 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>   |  | -   | 1.45 | 1.70 | V    |
|                 |                                 | I <sub>F</sub> = 6 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>  |  | -   | 1.80 | 2.20 | V    |
|                 |                                 | I <sub>F</sub> = 6 A; T <sub>j</sub> = 175 °C; <u>Fig. 5</u>  |  | -   | 2.00 | 2.30 | V    |
| I <sub>R</sub>  | reverse current                 | V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>   |  | -   | 0.3  | 30   | μA   |
|                 |                                 | V <sub>R</sub> = 650 V; T <sub>j</sub> = 175 °C; <u>Fig. 6</u>  |  | -   | 15   | 150  | μA   |
| Dynamic         | characteristics                 |   |  |     |      |      |      |
| $Q_r$           | recovered charge                | $I_F = 6 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$ |  | -   | 9    | -    | nC   |
| C <sub>d</sub>  | diode capacitance               | f = 1 MHz; V <sub>R</sub> = 1 V; T <sub>j</sub> = 25 °C   |  | -   | 201  | -    | pF   |
|                 |                                 | f = 1 MHz; V <sub>R</sub> = 300 V; T <sub>j</sub> = 25 °C   |  | -   | 24   | -    | pF   |
|                 |                                 | f = 1 MHz; V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C   |  | -   | 22   | -    | pF   |
| E <sub>as</sub> | non-repetitive avalanche energy | $I_R = 3.5 \text{ A}; L = 5 \text{ mH}; T_{j(init)} = 25 ^{\circ}\text{C}$                                      |  | 30  | -    | -    | mJ   |



 $V_o = 1.142 \text{ V}; R_s = 0.1756 \Omega$ 

(1)  $T_j = -55$  °C; typical values

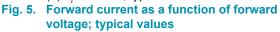
(2) T<sub>j</sub> = 0 °C; typical values

(3) T<sub>j</sub> = 25 °C; typical values

(4)  $T_j = 100 \,^{\circ}\text{C}$ ; typical values

(5)  $T_j = 150 \,^{\circ}\text{C}$ ; typical values

(6)  $T_j = 175$  °C; typical values



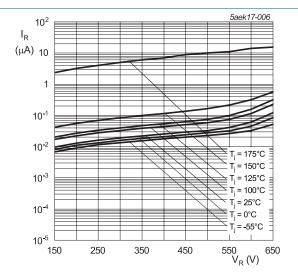
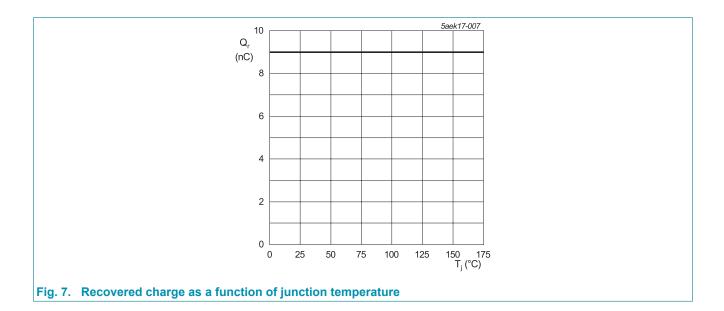
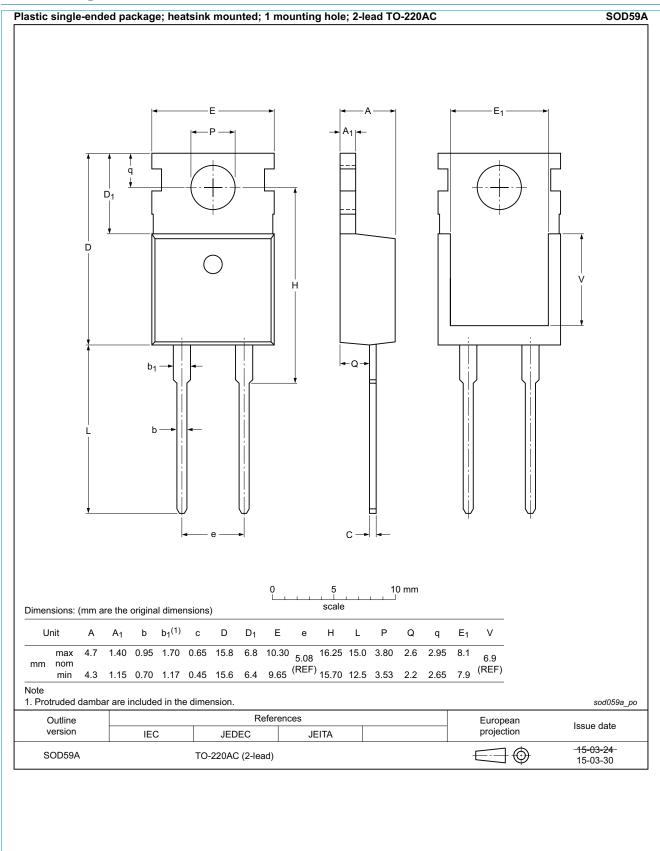


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value



# 11. Package outline



## 12. Legal information

#### Data sheet status

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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